GL150N04A8

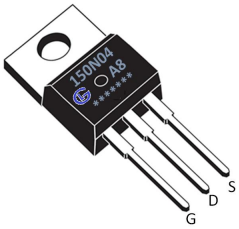
GL Silicon N-Channel Power MOSFET

V_{DSS}	40	V
I_D	150	A
P_D	130	W
$R_{DS(ON)type}$	3.0	mΩ

General Description

The GL150N04A8 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications. The package form is TO-220AB, which accords with the RoHS standard.

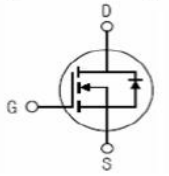
TO-220



Features

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Inner Equivalent Principium Chart



Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Absolute (Tc= 25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	40	V
I_D	Continuous Drain Current	150	A
	Continuous Drain Current T_C = 100 °C	90	A
I_{DM}	Pulsed Drain Current	400	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS} [a2]	Single Pulse Avalanche Energy	1100	mJ
E_{AR} [a1]	Avalanche Energy ,Repetitive	110	mJ
I_{AR} [a1]	Avalanche Current	50	A
dv/dt [a3]	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	130	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, −55 to 175	℃
T_L	Maximum Temperature for Soldering	300	℃

Electrical Characteristics (Tc=25℃ unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	BVdss Temperature Coefficient	I_D=250uA,Reference25℃	--	0.1	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS}=40V,V_{GS}=0V,T_a=25℃	--	--	1	μA
		V_{DS}=32V,V_{GS}=0V,T_a=125℃	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+20V	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-20V	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=40A	--	3.0	4.0	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	2	--	4	V
Pulse width tp≤380μs,δ≤2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	V_{DS}=10V,I_D=20A	25	--	--	S
C_{iss}	Input Capacitance	V_{GS}=0V,V_{DS}=20V f=1.0MHz	--	5400	--	pF
C_{oss}	Output Capacitance		--	970	--	
C_{rss}	Reverse Transfer Capacitance		--	380	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D=20A,V_{DD}=20V V_{GS}=10V,R_G=2.5Ω	--	23	--	ns
t_r	Rise Time		--	25	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	70	--	
t_f	Fall Time		--	30	--	
Q_g	Total Gate Charge	I_D=20A,V_{DD}=20V V_{GS}=10V	--	80	--	nC
Q_{gs}	Gate to Source Charge		--	11	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	18	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	150	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	400	A
V_{SD}	Diode Forward Voltage	I_S=40A,V_{GS}=0V	--	--	1.5	V
t_{rr}	Reverse Recovery Time	I_S=40A,T_j = 25°C	--	40	--	ns
Q_{rr}	Reverse Recovery Charge	dI_F/dt=100A/us,V_{GS}=0V	--	48	--	nC
Pulse width tp≤380μs,δ≤2%						

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta Jc}$	Junction-to-Case	1.15	℃/W

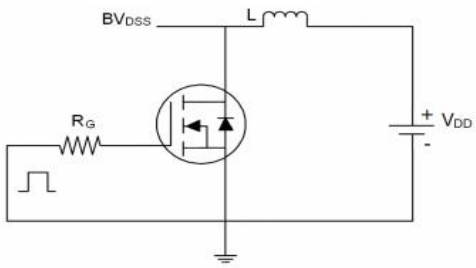
[a1]: Repetitive rating; pulse width limited by maximum junction temperature

[a2]: E_{AS} condition : Tj=25℃,V_{DD}= 30V,V_G=10V,L=0.5mH,R_g=25Ω

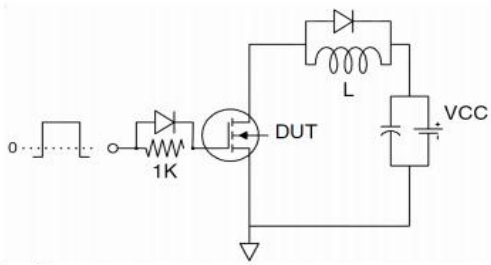
[a3]: I_{SD} =150A,di/dt ≤100A/us,V_{DD}≤BV_{DS}, Start T_J=25℃

Test Circuits

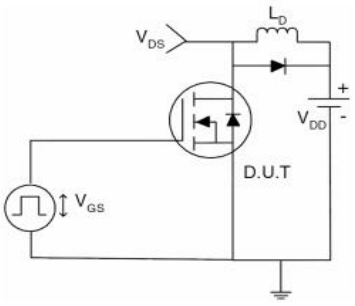
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



Characteristics Curves

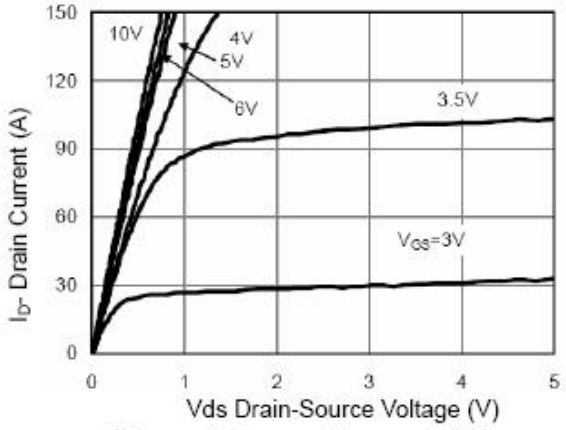


Figure 1 Output Characteristics

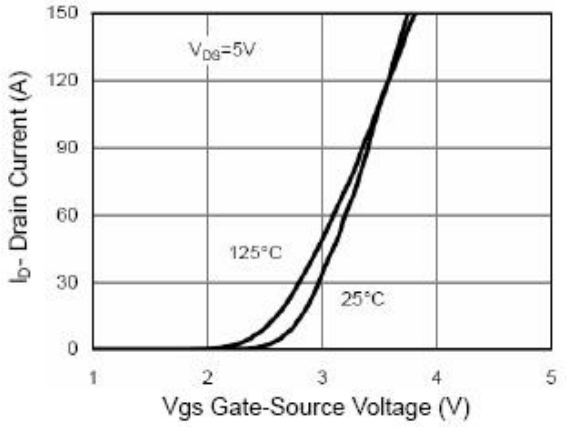


Figure 2 Transfer Characteristics

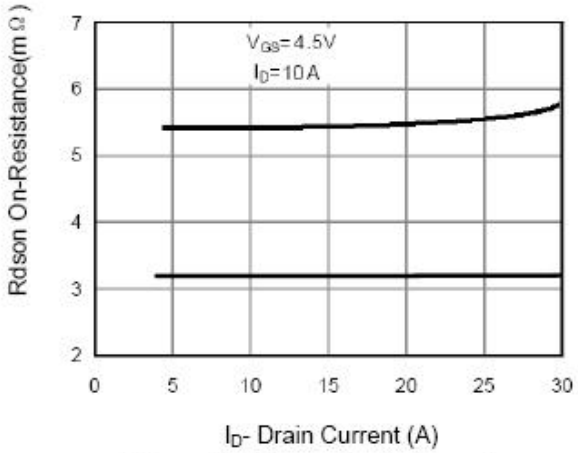


Figure 3 Rdson- Drain Current

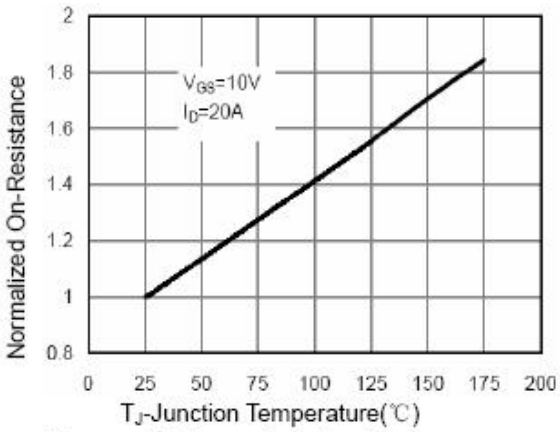


Figure 4 Rdson-JunctionTemperature

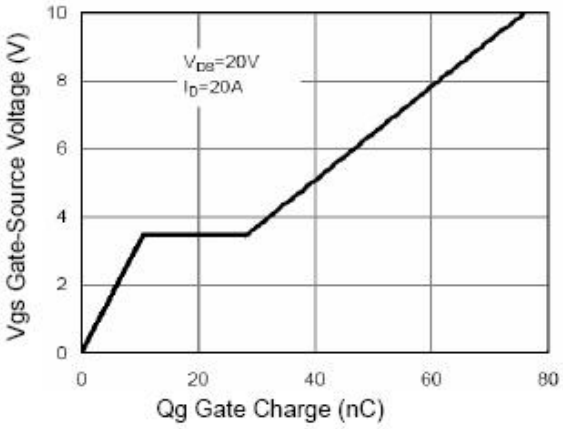


Figure 5 Gate Charge

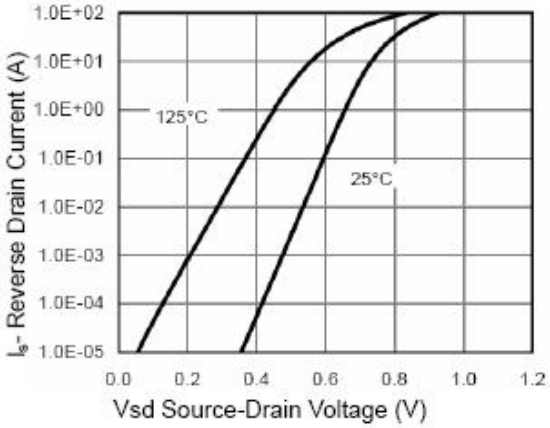


Figure 6 Source- Drain Diode Forward

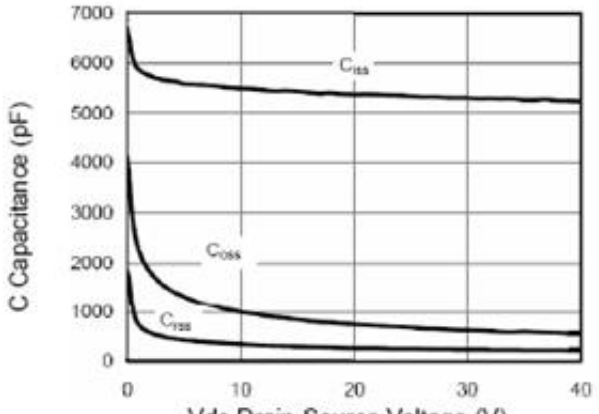


Figure 7 Capacitance vs Vds

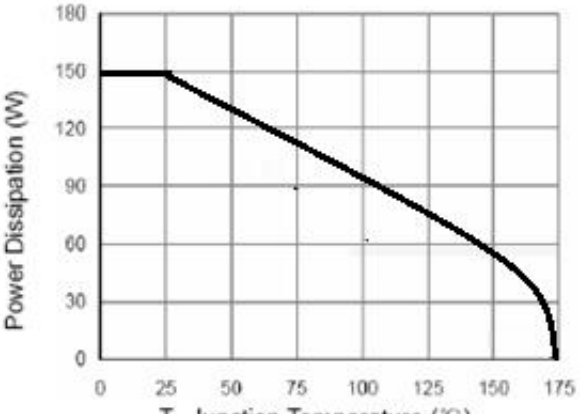


Figure 9 Power De-rating

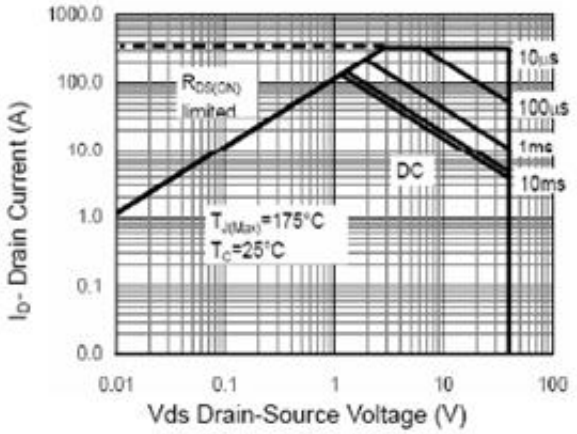


Figure 8 Safe Operation Area

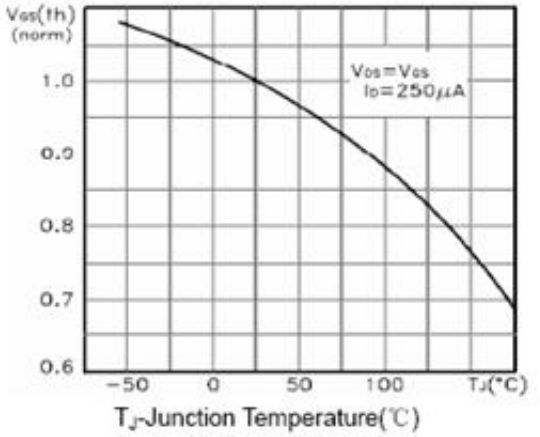


Figure 10 $V_{GS(th)}$ vs Junction Temperature

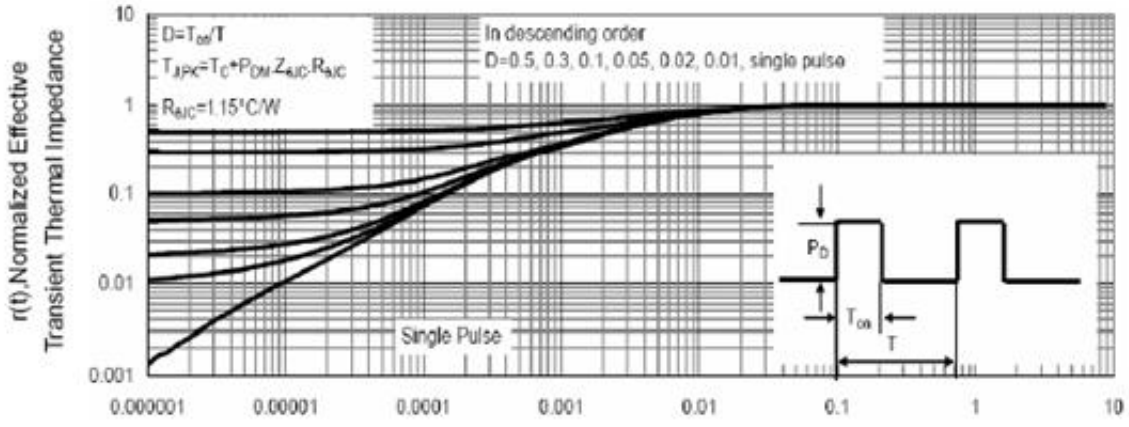


Figure 11 Normalized Maximum Transient Thermal Impedance